

TC74VCX16843FT

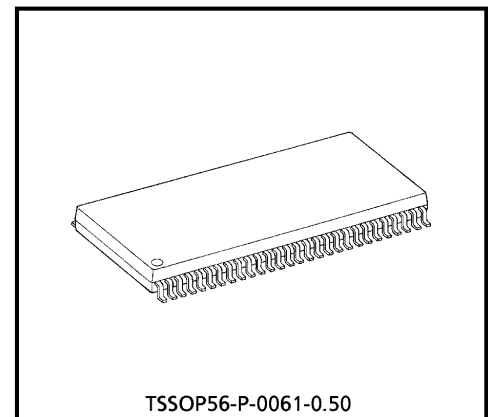
LOW-VOLTAGE 18-BIT D-TYPE LATCH WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

The TC74VCX16843FT is a high performance CMOS 18-bit D-TYPE LATCH. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation. It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

The TC74VCX16843FT can be used as two 9-bit latches or one 18-bit latch. The 18 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 9-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs. $\overline{\text{CLR}}$ and $\overline{\text{PR}}$ are independent of the LE and are accomplished by setting the appropriate input low.

When the $\overline{\text{OE}}$ input is high, the outputs are in a high impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.



TSSOP56-P-0061-0.50

Weight : 0.25 g (Typ.)

FEATURES

- Low Voltage Operation : $V_{CC} = 1.8 \sim 3.6V$
- High Speed Operation : $t_{pd} = 3.0 \text{ ns (max) at } V_{CC} = 3.0 \sim 3.6 V$
 $t_{pd} = 3.7 \text{ ns (max) at } V_{CC} = 2.3 \sim 2.7 V$
 $t_{pd} = 7.4 \text{ ns (max) at } V_{CC} = 1.8 V$
- 3.6 V Tolerant inputs and outputs.
- Output Current : $I_{OH}/I_{OL} = \pm 24 \text{ mA (min) at } V_{CC} = 3.0 V$
 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) at } V_{CC} = 2.3 V$
 $I_{OH}/I_{OL} = \pm 6 \text{ mA (min) at } V_{CC} = 1.8 V$
- Latch-up Performance : $\pm 300 \text{ mA}$
- ESD Performance : Human Body Model $> \pm 2000 V$
Machine Model $> \pm 200 V$
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 1)

(Note 1) : To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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FUNCTION TABLE (each 9-bit latch)

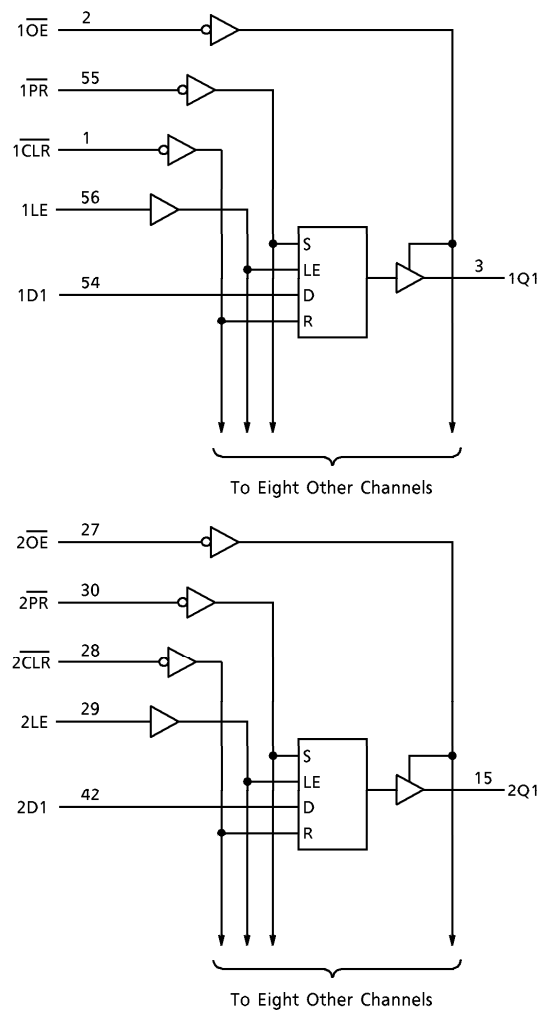
INPUTS					OUTPUT Q
$\overline{\text{PR}}$	$\overline{\text{CLR}}$	$\overline{\text{OE}}$	LE	D	
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Qn
X	X	H	X	X	Z

X : Don't care

Z : High impedance

Qn : Q outputs are latched at the time when the LE input is taken to a low logic level.

SYSTEM DIAGRAM



MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	$-0.5 \sim 4.6$	V
DC Input Voltage	V_{IN}	$-0.5 \sim 4.6$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim 4.6$ (Note 1) $-0.5 \sim V_{CC} + 0.5$ (Note 2)	V
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	± 50 (Note 3)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC} / I_{GND}	± 100	mA
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

(Note 1) : Off-State

(Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) : $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	$1.8 \sim 3.6$ $1.2 \sim 3.6$ (Note 4)	V
Input Voltage	V_{IN}	$-0.3 \sim 3.6$	V
Output Voltage	V_{OUT}	$0 \sim 3.6$ (Note 5) $0 \sim V_{CC}$ (Note 6)	V
Output Current	I_{OH} / I_{OL}	± 24 (Note 7) ± 18 (Note 8) ± 6 (Note 9)	mA
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise And Fall Time	dt / dv	$0 \sim 10$ (Note 10)	ns / V

(Note 4) : Data Retention Only

(Note 5) : Off-State

(Note 6) : High or Low State

(Note 7) : $V_{CC} = 3.0 \sim 3.6$ V(Note 8) : $V_{CC} = 2.3 \sim 2.7$ V(Note 9) : $V_{CC} = 1.8$ V(Note 10) : $V_{IN} = 0.8 \sim 2.0$ V, $V_{CC} = 3.0$ V

ELECTRICAL CHARACTERISTICSDC characteristics (Ta = -40~85°C, 2.7 V < V_{CC} ≤ 3.6 V)

PARAMETER		SYMBOL	TEST CONDITION		V _{CC} (V)	MIN	MAX	UNIT
Input Voltage	"H" Level	V _{IH}			2.7~3.6	2.0	—	V
	"L" Level	V _{IL}			2.7~3.6	—	0.8	V
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = - 100 μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = - 12 mA	2.7	2.2	—	
				I _{OH} = - 18 mA	3.0	2.4	—	
				I _{OH} = - 24 mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	—	0.2	V
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 18 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.7~3.6	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	—	± 20.0	
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7~3.6	—	750	μA

ELECTRICAL CHARACTERISTICSDC characteristics (Ta = -40~85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

PARAMETER		SYMBOL	TEST CONDITION			MIN	MAX	UNIT
					V _{CC} (V)			
Input Voltage	“H” Level	V _{IH}			2.3~2.7	1.6	—	V
	“L” Level	V _{IL}			2.3~2.7	—	0.7	V
Output Voltage	“H” Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.3	2.0	—	
				I _{OH} = -12 mA	2.3	1.8	—	
				I _{OH} = -18 mA	2.3	1.7	—	
	“L” Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2	V
				I _{OL} = 12 mA	2.3	—	0.4	
				I _{OL} = 18 mA	2.3	—	0.6	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.3~2.7	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	—	± 20.0	

ELECTRICAL CHARACTERISTICSDC characteristics ($T_a = -40\sim 85^\circ\text{C}$, $1.8\text{ V} \leq V_{CC} < 2.3\text{ V}$)

PARAMETER		SYMBOL	TEST CONDITION			MIN	MAX	UNIT	
			V _{CC} (V)						
Input Voltage	“H” Level	V _{IH}	1.8~2.3			0.7 × V _{CC}	—	V	
	“L” Level	V _{IL}	1.8~2.3			—	0.2 × V _{CC}	V	
Output Voltage	“H” Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = − 100 μA	1.8	V _{CC} − 0.2	—	V	
				I _{OH} = − 6 mA	1.8	1.4	—		
	“L” Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	V	
				I _{OL} = 6 mA	1.8	—	0.3		
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V			1.8	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V			1.8	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V			0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND			1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V			1.8	—	± 20.0	

AC characteristics ($T_a = -40 \sim 85^\circ\text{C}$, Input $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN	MAX	UNIT
Propagation Delay Time (D-Q)	t_{pLH} t_{pHL}	(Fig.1, 2)	1.8	1.5	7.4	MHz
			2.5 ± 0.2	0.8	3.7	
			3.3 ± 0.3	0.6	3.0	
Propagation Delay Time (LE-Q)	t_{pLH} t_{pHL}	(Fig.1, 2)	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.4	
			3.3 ± 0.3	0.6	3.5	
Propagation Delay Time (PR-Q)	t_{pLH}	(Fig.1, 3)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.6	
			3.3 ± 0.3	0.6	4.0	
Propagation Delay Time ($\overline{\text{CLR}}$ -Q)	t_{pHL}	(Fig.1, 3)	1.8	1.5	9.2	ns
			2.5 ± 0.2	0.8	4.6	
			3.3 ± 0.3	0.6	3.7	
3-State Output Enable Time	t_{pZL} t_{pZH}	(Fig.1, 4)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	3.8	
3-State Output Disable Time	t_{pLZ} t_{pHZ}	(Fig.1, 4)	1.8	1.5	7.6	ns
			2.5 ± 0.2	0.8	4.2	
			3.3 ± 0.3	0.6	3.7	
Minimum Pulse Width (LE, PR, CLR)	$t_w (H)$ $t_w (L)$	(Fig.1, 2, 3)	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Set-up Time	t_s	(Fig.1, 2)	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Hold Time	t_h	(Fig.1, 2)	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Minimum Removal Time	t_{rem}	(Fig.1, 5)	1.8	4.0	—	ns
			2.5 ± 0.2	3.0	—	
			3.3 ± 0.3	2.0	—	
Output to Output Skew	t_{osLH} t_{osHL}	(Note 11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

(Note 11) : Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics ($T_a = 25^\circ\text{C}$, Input $t_r = t_f = 2.0\text{ ns}$, $C_L = 30\text{ pF}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	TYP.	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$V_{IH} = 1.8\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	1.8	0.25	V
		$V_{IH} = 2.5\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	2.5	0.6	
		$V_{IH} = 3.3\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	3.3	0.8	
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	$V_{IH} = 1.8\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	1.8	-0.25	V
		$V_{IH} = 2.5\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	2.5	-0.6	
		$V_{IH} = 3.3\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	3.3	-0.8	
Quiet Output Minimum Dynamic V_{OH}	V_{OHV}	$V_{IH} = 1.8\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	1.8	1.5	V
		$V_{IH} = 2.5\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	2.5	1.9	
		$V_{IH} = 3.3\text{ V}$, $V_{IL} = 0\text{ V}$ (Note 12)	3.3	2.2	

(Note 12) : Parameter guaranteed by design.

Capacitive characteristics ($T_a = 25^\circ\text{C}$)

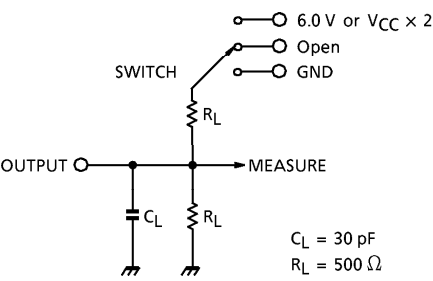
PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	TYP.	UNIT
Input Capacitance	C_{IN}		1.8, 2.5, 3.3	6	pF
Output Capacitance	C_O		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10\text{ MHz}$ (Note 13)	1.8, 2.5, 3.3	20	pF

(Note 13) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/18 \text{ (per bit)}$$

TEST CIRCUIT
Fig.1



PARAMETER	SWITCH
t_{pLH} , t_{pHL}	Open
t_{pLZ} , t_{pZL}	6.0 V @ $V_{CC} = 3.3 \pm 0.3$ V $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2$ V @ $V_{CC} = 1.8$ V
t_{pHZ} , t_{pZH}	GND

AC WAVEFORM
Fig.2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

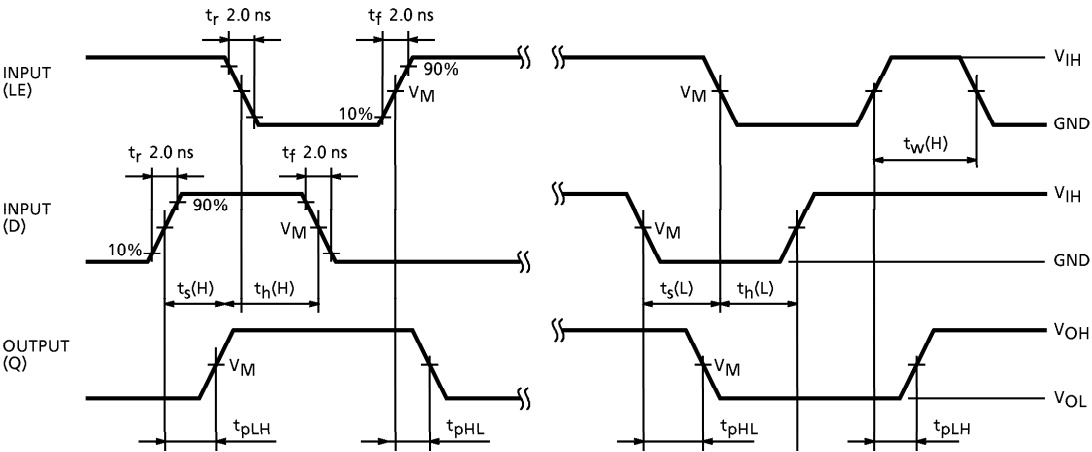


Fig.3 t_{pLH} , t_{pHL} , t_w

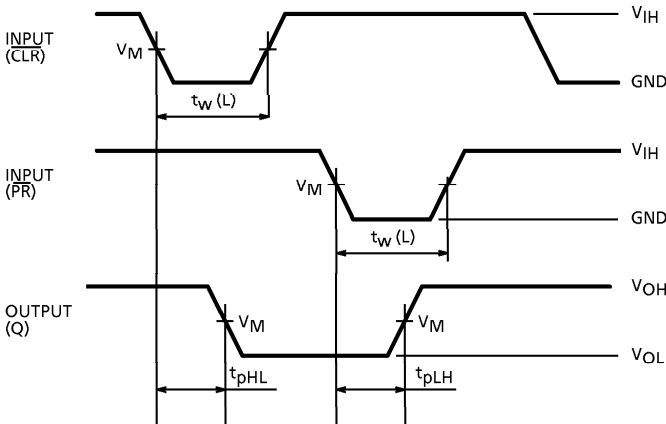
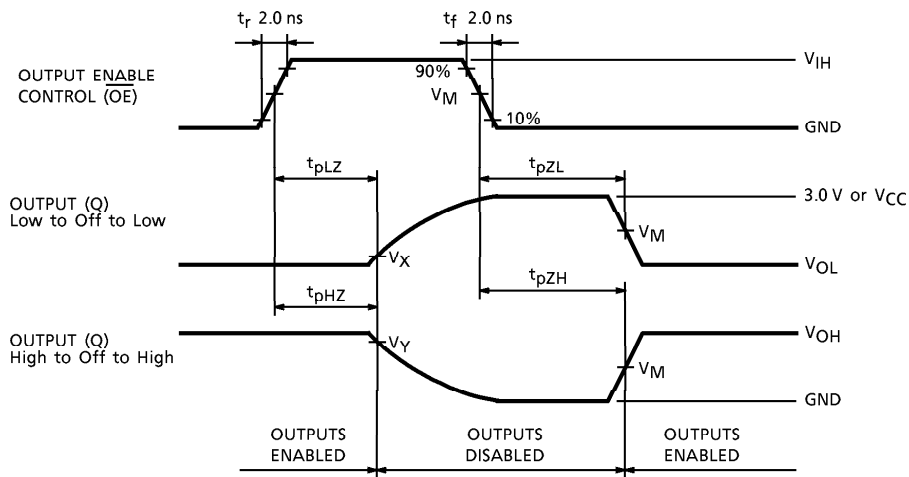
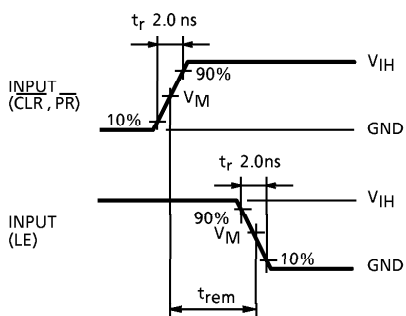


Fig.4 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}



SYMBOL	V _{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} / 2	V _{CC} / 2
V _X	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
V _Y	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V

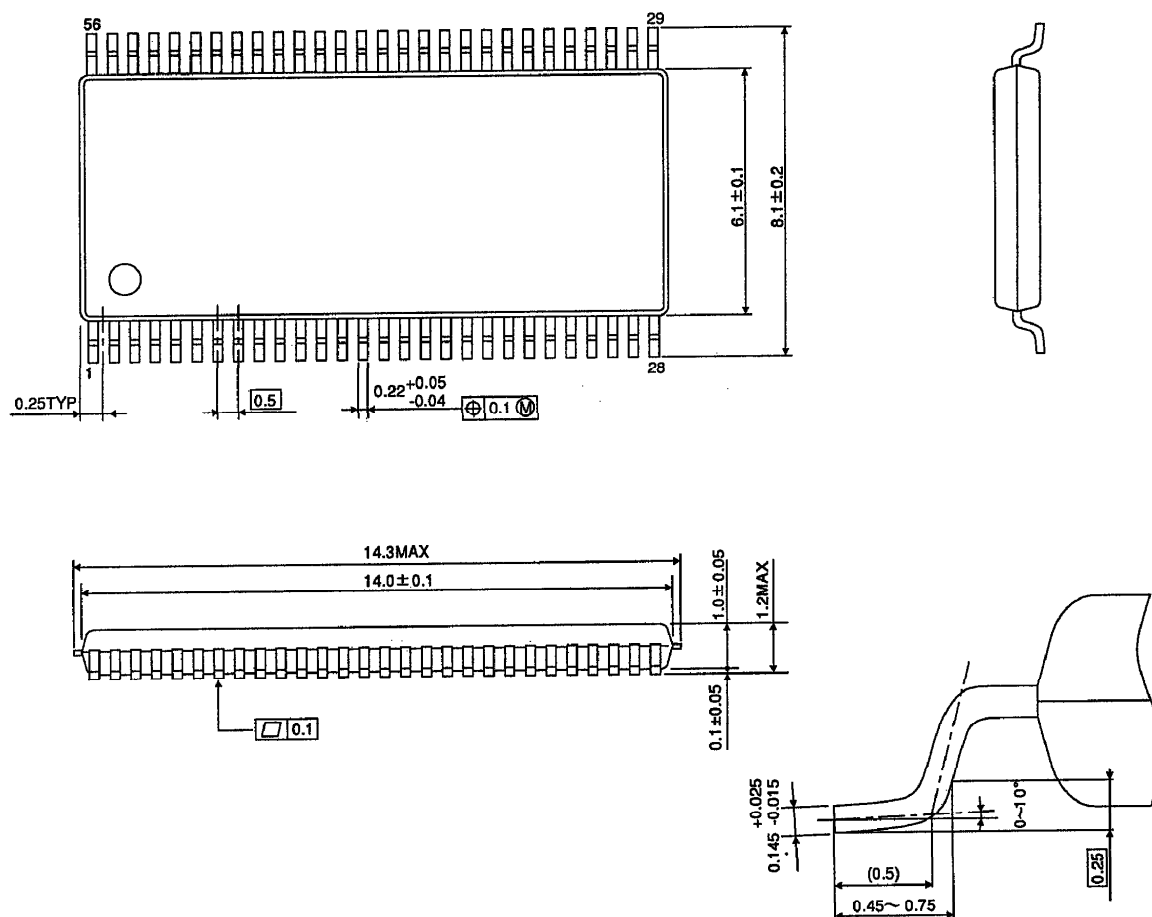
Fig.5 t_{rem}



OUTLINE DRAWING

TSSOP56-P-0061-0.50

Unit : mm



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